

Silicon NPN Power Transistor

KSD5075

DESCRIPTION

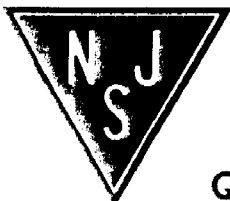
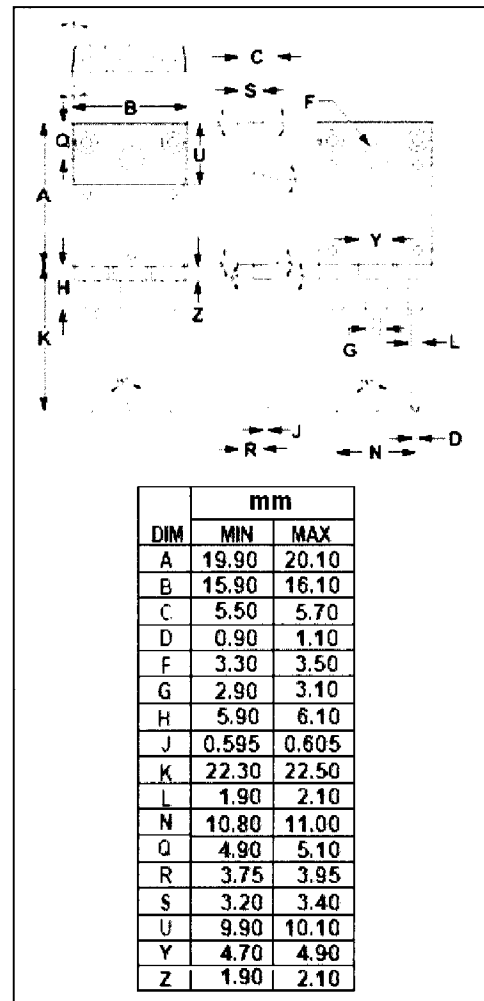
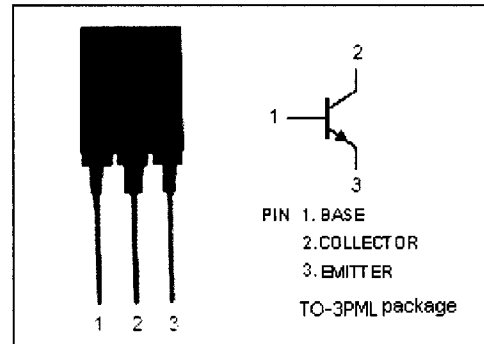
- High Breakdown Voltage-
 : $V_{CBO} = 1500V$ (Min)
- High Switching Speed
- High Reliability

APPLICATIONS

- Designed for color TV horizontal output applications

ABSOLUTE MAXIMUM RATINGS ($T_a = 25^\circ C$)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	1500	V
V_{CEO}	Collector-Emitter Voltage	800	V
V_{EBO}	Emitter-Base Voltage	6	V
I_C	Collector Current- Continuous	3.5	A
I_{CP}	Collector Current-Peak	10	A
P_C	Collector Power Dissipation @ $T_C = 25^\circ C$	50	W
T_J	Junction Temperature	150	$^\circ C$
T_{stg}	Storage Temperature Range	-55~150	$^\circ C$



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ELECTRICAL CHARACTERISTICS

$T_C=25^\circ\text{C}$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	$I_C = 2.5A; I_B = 0.8A$			8.0	V
$V_{BE(sat)}$	Base-Emitter Saturation Voltage	$I_C = 2.5A; I_B = 0.8A$			1.5	V
I_{CBO}	Collector Cutoff Current	$V_{CB} = 800V; I_E = 0$			10	μA
I_{EBO}	Emitter Cutoff Current	$V_{EB} = 5V; I_C = 0$			1	mA
h_{FE}	DC Current Gain	$I_C = 0.5A; V_{CE} = 5V$	8			
f_T	Current-Gain—Bandwidth Product	$I_C = 0.5A; V_{CE} = 10V$		3		MHz
t_f	Fall Time	$I_C = 3A, I_{B1} = 0.8A; I_{B2} = -1.6A$ $R_L = 66.7 \Omega; V_{CC} = 200V$			0.4	μs